

Amendments to the Specification:

- Please replace the Abstract with the following rewritten Abstract:

ABSTRACT OF THE DISCLOSURE

~~Although there is provided a high light transmittance of an emitted light by a ITO electrode film conventionally employed, there occurs a formation of a Schottky type contact between the ITO electrode film and a p type GaN system semiconductor layer, thus resulting in a not uniform flow of an electric current. It is an object of the present invention to provide a semiconductor light emitting device constituted by forming a transparent electrode, which facilitates acquiring an ohmic property, to be replaced by an ITO electrode film, at the light extracting or light exit side of the GaN system semiconductor light emitting device, so as to improve a light emission efficiency and a radiation extracting efficiency or a light exit efficiency of a GaN system semiconductor light emitting device.~~

In order to accomplish the above mentioned object, the present invention provides a semiconductor light emitting device ~~comprising including~~ a light emission layer, ~~consisting of having~~ a GaN system semiconductor, which is interposed between an n type GaN system semiconductor layer and a p type GaN system semiconductor layer, wherein there is provided a Ga-doped $Mg_zZn_{1-z}O$ ($0 \leq z < 1$) electrode film.

Appl. No. 10/763,137
Amdt. Dated May 12, 2005
Reply to Office Action of April 4, 2005

Attorney Docket No. 88519.0002
Customer No.: 26021

- Please replace the Title beginning at page 28, line 1, with the following rewritten Title:

DESCRIPTION
~~SEMICONDUCTOR LIGHT EMITTING DEVICE~~
GaN System Semiconductor Light Emitting Device Excellent in Light
Emission Efficiency and Light Extracting Efficiency